IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Shunpei Yamazaki et al. Art Unit : Unknown
Serial No. : New application Examiner : Unknown
Filed : December 20, 2001
Title : LIGHT EMITTING DEVICE AND METHOD OF MANUFACTURING THE SAME

Commissioner for Patents
Washington, D.C. 20231

PRELIMINARY AMENDMENT

Prior to examination, please amend the application as follows:

In the claims:

Amend claims 4, 10, 18, 24-26, 39, 45, 46, 50, 55, 61, 65, 69-71 and 74-76 as follows:

4. A light emitting device according to claim 1, wherein the conductor is made of the same material as a gate electrode of the switching element.

10. A light emitting device according to claim 7, wherein the conductor is made of the same material as a gate electrode of the switching element.

18. A light emitting device according to claim 13, wherein at least one of the first conductive coating and the second conductive coating is formed by a printing method.

24. A light emitting device according to claim 21, wherein the first conductor and the second conductor are simultaneously formed.

25. A light emitting device according to claim 21, wherein at least one of the first conductive coating and the second conductive coating is made of the same material as a gate electrode of the switching element.

26. A light emitting device according to claim 21, wherein at least one of the first conductive coating and the second conductive coating is formed by a printing method.

39. A light emitting device according to claim 37, wherein the first, second, and third switching elements are p-channel thin film transistors.

45. A light emitting device according to claim 37, wherein the conductor is made of the same material as a gate electrode of the first, second, and third switching element.

46. A light emitting device according to claim 37, wherein at least one of the first, second, and third switching element comprises at least one thin film transistor.

50. A light emitting device according to claim 49, wherein the impurity region in at least one of the first, second, and third switching elements comprises a region having a concentration gradient at least at an impurity concentration of 1×10^{17} to 1×10^{18} / cm^3, and the impurity concentration is increased as a distance from the channel forming region increases.

55. A light emitting device according to claim 52, wherein the first, second, and third switching elements are p-channel thin film transistors.

61. A light emitting device according to claim 52, wherein the conductor is made of the same material as a gate electrode of the switching element.

65. A light emitting device according to claim 64, wherein the impurity region in at least one of the first, second, and third switching elements comprises a region having a concentration gradient at least at an impurity concentration of 1×10^{17} to 1×10^{18} / cm^3, and the impurity concentration is increased as a distance from the channel forming region increases.

69. A method of manufacturing a light emitting device according to claim 67, wherein forming the conductive coating further comprises connecting the conductor with a wiring to be the same potential.

70. A method of manufacturing a light emitting device according to claim 69, further comprising separating the wiring using a laser light after forming the conductive coating.

71. A method of manufacturing a light emitting device according to claim 69, further comprising separating the wiring simultaneously with the substrate after plating.

74. A method of manufacturing a light emitting device according to claim 72, wherein forming the conductive coating further comprises connecting the conductor with a wiring to be the same potential.

75. A method of manufacturing a light emitting device according to claim 74, further comprising separating the wiring using a laser light after forming the conductive coating.

76. A method of manufacturing a light emitting device according to claim 74, further comprising separating the wiring simultaneously with the substrate after plating.

REMARKS

The amendments to the claims made herein are to correct minor grammatical errors and to place the application in better form for examination. No new matter is added.

Attached is a marked-up version of the changes being made by the current amendment.

Applicants ask that all claims be examined. Please apply any charges or credits to Deposit Account No. 06-1050.

Respectfully submitted,

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Version with markings to show changes made

In the claims:

Claims 4, 10, 18, 24-26, 39, 45, 46, 50, 55, 61, 65, 69-71 and 74-76 have been amended as follows:

4. (Amended) A light emitting device according to **[any one of claims]** claim 1, wherein the conductor is made of the same material as a gate electrode of the switching element.

10. (Amended) A light emitting device according to **[any one of claims]** claim 7, wherein the conductor is made of the same material as a gate electrode of the switching element.

18. (Amended) A light emitting device according to **[any one of claims]** claim 13, wherein at least one of the first conductive coating and the second conductive coating is formed by a printing method.

24. (Amended) A light emitting device according to **[any one of claims]** claim 21, wherein the first conductor and the second conductor are simultaneously formed.

25. (Amended) A light emitting device according to **[any one of claims]** claim 21, wherein at least one of the first conductive coating and the second conductive coating is made of the same material as a gate electrode of the switching element.

26. (Amended) A light emitting device according to **[any one of claims]** claim 21, wherein at least one of the first conductive coating and the second conductive coating is formed by a printing method.

39. (Amended) A light emitting device according to claim 37, wherein the first,

second, and third switching elements are **[a]** p-channel thin film transistors.

45. (Amended) A light emitting device according to **[claims]** claim 37, wherein the conductor is made of the same material as a gate electrode of the first, second, and third switching element.

46. (Amended) A light emitting device according to claim 37, wherein at least one of the first, second, and third switching element comprises at least one **[tin]** thin film transistor.

50. (Amended) A light emitting device according to claim 49, wherein the impurity region in at least one of the first, second, and third switching elements comprises a region having a concentration gradient at least at an impurity concentration of 1×10^{17} to 1×10^{18} / cm^3, and the impurity concentration is increased **[with increasing]** as a distance from the channel forming region increases.

55. (Amended) A light emitting device according to claim 52, wherein the first, second, and third switching elements are **[a]** p-channel thin film transistors.

61. (Amended) A light emitting device according to **[claims]** claim 52, wherein the conductor is made of the same material as a gate electrode of the switching element.

65. (Amended) A light emitting device according to claim 64, wherein the impurity region in at least one of the first, second, and third switching elements comprises a region having a concentration gradient at least at an impurity concentration of 1×10^{17} to 1×10^{18} / cm^3, and the impurity concentration is increased **[with increasing]** as a distance from the channel forming region increases.

69. (Amended) A method of manufacturing a light emitting device according to **[any one of claims]** claim 67, wherein forming the conductive coating further comprises

connecting the conductor **[is connected]** with a wiring to be the same potential **[in the step using the electroplating method]**.

70. (Amended) A method of manufacturing a light emitting device according to claim 69, **[wherein]** further comprising separating the wiring **[is separated by]** using a laser light after forming the conductive coating.

71. (Amended) A method of manufacturing a light emitting device according to claim 69, **[wherein]** further comprising separating the wiring **[is separated]** simultaneously with the substrate after plating.

74. (Amended) A method of manufacturing a light emitting device according to **[any one of]** claim 72, wherein forming the conductive coating further comprises connecting the conductor **[is connected]** with a wiring to be the same potential **[in the step using the electroplating method]**.

75. (Amended) A method of manufacturing a light emitting device according to claim 74, **[wherein]** further comprising separating the wiring **[is separated by]** using a laser light after forming the conductive coating.

76. (Amended) A method of manufacturing a light emitting device according to claim 74, **[wherein]** further comprising separating the wiring **[is separated]** simultaneously with the substrate after plating.